SN65C3232E, SN75C3232E 3-V TO 5.5-V TWO-CHANNEL RS-232 1-MBIT/S LINE DRIVERS/RECEIVERS

TRUMENTS www.ti.com

WITH ±15-kV IEC ESD PROTECTION SLLS697A-DECEMBER 2005-REVISED DECEMBER 2007

FEATURES

- Operate With 3-V to 5.5-V V_{CC} Supply
- Operate up to 1 Mbit/s
- Low Supply Current . . . 300 μA Typ
- External Capacitors . . . 4 \times 0.1 μF
- Accept 5-V Logic Input With 3.3-V Supply
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection for RS-232 Pins
 - ±15-kV Human-Body Model (HBM)
 - ±15-kV IEC 61000-4-2 Air-Gap Discharge
 - ±8-kV IEC 61000-4-2 Contact Discharge

APPLICATIONS

- Battery-Powered Systems
- PDAs
- Notebooks
- Laptops
- Palmtop PCs
- Hand-Held Equipment

DESCRIPTION/ORDERING INFORMATION

The SN65C3232E and SN75C3232E consist of two line drivers, two line receivers, and a dual charge-pump circuit with \pm 15-kV ESD protection pin to pin (serial-port connection pins, including GND). These devices provide the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The devices operate at data signaling rates up to 1 Mbit/s and a driver output slew rate of 14 V/µs to 150 V/µs.

ORDERING INFORMATION

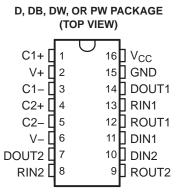
T _A PAC		CKAGE ⁽¹⁾⁽²⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING
	SOIC – D	Tube of 40	SN65C3232ED	65C3232E
	50IC - D	Reel of 2500	SN65C3232EDR	0003232E
	SOIC - DW	Tube of 40	SN65C3232EDW	65022225
–40°C to 85°C	50IC - DW	Reel of 2000	SN65C3232EDWR	65C3232E
	SSOP – DB	Reel of 2000	SN65C3232EDBR	MU232E
		Tube of 90	SN65C3232EPW	MU232E
	TSSOP – PW	Reel of 2000	SN65C3232EPWR	MU232E
		Tube of 40	SN75C3232ED	75022205
	SOIC – D	Reel of 2500	SN75C3232EDR	75C3232E
	SOIC – DW	Tube of 40	SN75C3232EDW	75022205
0°C to 70°C	50IC - DW	Reel of 2000	SN75C3232EDWR	75C3232E
	SSOP – DB	Reel of 2000	SN75C3232EDBR	MY232E
		Tube of 90	SN75C3232EPW	MY222E
	TSSOP – PW Reel of 2000		SN75C3232EPWR	MY232E

(1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

(2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.



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SN65C3232E, SN75C3232E 3-V TO 5.5-V TWO-CHANNEL RS-232 1-MBIT/S LINE DRIVERS/RECEIVERS WITH ±15-kV IEC ESD PROTECTION



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TEMPERATURE RANGE	PART NO.	NO. OF DRIVERS	NO. OF RECEIVERS	ESD	SUPPLY V _{CC} (V)	FEATURE	PIN/PACKAGE
	SN65C3221E	1	1	±15-kV Air-Gap, ±8-kV Contact, ±15-kV HBM	3.3 or 5	Auto powerdown	16-pin SOIC, SSOP, TSSOP
	SN65C3232E	2	2	±15-kV Air-Gap, ±8-kV Contact, ±15-kV HBM	3.3 or 5	Low pin count	16-pin SOIC, SSOP, TSSOP
	MAX3227I	1	1	±8-kV Air-Gap, ±8-kV Contact, ±15-kV HBM	3.3 or 5	Auto powerdown plus, ready signal	16-pin SSOP
–40°C to 85°C	SN65C3221	1	1	±15-kV HBM	3.3 or 5	Auto powerdown	16-pin SOIC, SSOP, TSSOP
	SN65C3223	2	2	±15-kV HBM	3.3 or 5	Auto powerdown, enable signal	20-pin SOIC, SSOP, TSSOP
	SN65C3222	2	2	±15-kV HBM	3.3 or 5	Enable, powerdown signal	20-pin SOIC, SSOP, TSSOP
-	SN65C3232	2	2	±15-kV HBM	3.3 or 5	Low pin count	16-pin SOIC, SSOP, TSSOP
	SN65C3238	5	3	±15-kV HBM	3.3 or 5	Auto powerdown plus	28-pin SOIC, SSOP, TSSOP
-	SN65C3243	3	5	±15-kV HBM	3.3 or 5	Auto powerdown	28-pin SOIC, SSOP, TSSOP
	SN75C3221E	1	1	±15-kV Air-Gap, ±8-kV Contact, ±15-kV HBM	3.3 or 5	Auto powerdown	16-pin SOIC, SSOP, TSSOP
	SN75C3232E	2	2	±15-kV Air-Gap, ±8-kV Contact, ±15-kV HBM	3.3 or 5	Low pin count	16-pin SOIC, SSOP, TSSOP
	MAX3227C	1	1	±8-kV Air-Gap, ±8-kV Contact, ±15-kV HBM	3.3 or 5	Auto powerdown plus, ready signal	16-pin SSOP
0°C to 70°C	SN75C3221	1	1	±15-kV HBM	3.3 or 5	Auto powerdown	16-pin SOIC, SSOP, TSSOP
	SN75C3223	2	2	±15-kV HBM	3.5 or 5	Auto powerdown, enable signal	20-pin SOIC, SSOP, TSSOP
-	SN75C3222	2	2	±15-kV HBM	3.3 or 5	Enable, powerdown signal	20-pin SOIC, SSOP, TSSOP
-	SN75C3232	2	2	±15-kV HBM	3.3 or 5	Low pin count	16-pin SOIC, SSOP, TSSOP
	SN75C3238	5	3	±15-kV HBM	3.3 or 5	Auto powerdown plus	28-pin SOIC, SSOP, TSSOP
-	SN75C3243	3	5	±15-kV HBM	3.3 or 5	Auto powerdown	28-pin SOIC, SSOP, TSSOP

Table 1. 1-Mbit/s RS-232 Parts



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FUNCTION TABLES

EACH DRIVER⁽¹⁾

INPUT DIN	OUTPUT DOUT
L	Н
н	L

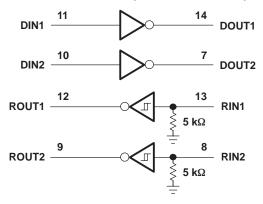
(1) H = high level, L = low level

EACH RECEIVER⁽¹⁾

INPUT RIN	OUTPUT ROUT
L	Н
н	L
Open	Н

 H = high level, L = low level, Open = input disconnected or connected driver off

LOGIC DIAGRAM (POSITIVE LOGIC)



SN65C3232E, SN75C3232E 3-V TO 5.5-V TWO-CHANNEL RS-232 1-MBIT/S LINE DRIVERS/RECEIVERS WITH ±15-kV IEC ESD PROTECTION



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Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range ⁽²⁾		-0.3	6	V
V+	Positive output supply voltage range ⁽²⁾		-0.3	7	V
V–	Negative output supply voltage range ⁽²⁾		0.3	-7	V
V+ - V-	Supply voltage difference ⁽²⁾			13	V
VI		Drivers	-0.3	6	
	Input voltage range	Receivers	-25	25	V
.,	Output voltage range	Drivers	-13.2	13.2	
Vo		Receivers	-0.3	V _{CC} + 0.3	V
		D package		82	
0	Declares the resulting a damage $(3)(4)$	DB package		46	°C/W
θ_{JA}	Package thermal impedance ⁽³⁾⁽⁴⁾	DW package		57	°C/W
		PW package		108	
TJ	Operating virtual junction temperature	I		150	°C
T _{stg}	Storage temperature range		-65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltages are with respect to network GND.

(3) Maximum power dissipation is a function of $T_J(max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) - T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.

(4) The package thermal impedance is calculated in accordance with JESD 51-7.

Recommended Operating Conditions⁽¹⁾

				MIN	NOM	MAX	UNIT
	Supply voltage		$V_{CC} = 3.3 V$	3	3.3	3.6	V
	Supply voltage		$V_{CC} = 5 V$	4.5	5	5.5	v
V	Driver high-level input voltage	DIN	$V_{CC} = 3.3 V$	2			V
VIH		DIN	$V_{CC} = 5 V$	2.4			v
V_{IL}	Driver low-level input voltage		DIN			0.8	V
V	Driver input voltage		DIN	0		5.5	V
VI	Receiver input voltage	·	-25		25	v	
т	Operating free-air temperature		SN65C3232E	-40		85	°C
T _A			SN75C3232E	0		70	-C

(1) Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V (see Figure 4).

Electrical Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP ⁽²⁾	MAX	UNIT
I _{CC}	Supply current	No load,	V_{CC} = 3.3 V or 5 V		0.3	1	mA

(1) Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V (see Figure 4). (2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.



DRIVER SECTION

Electrical Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDIT	MIN	TYP ⁽²⁾	MAX	UNIT	
V _{OH}	High-level output voltage	DOUT at $R_L = 3 k\Omega$ to GND,	DIN = GND	5	5.5		V
V _{OL}	Low-level output voltage	DOUT at $R_L = 3 k\Omega$ to GND,	$DIN = V_{CC}$	-5	-5.4		V
I _{IH}	High-level input current	$V_{I} = V_{CC}$			±0.01	±1	μΑ
I _{IL}	Low-level input current	V _I at GND			±0.01	±1	μΑ
I _{OS} ⁽³⁾	Short-circuit output current	V _{CC} = 3.6 V,	$V_0 = 0 V$		±35	±60	
IOS (V _{CC} = 5.5 V,	$V_0 = 0 V$		±35	±90	mA
r _o	Output resistance	V_{CC} , V+, and V- = 0 V,	$V_0 = \pm 2 V$	300	10M		Ω

(1) Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V (see Figure 4).

(2)

All typical values are at $V_{CC} = 3.3$ V or $V_{CC} = 5$ V, and $T_A = 25^{\circ}$ C. Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one (3) output should be shorted at a time.

Switching Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS			TYP ⁽²⁾	MAX	UNIT
	Maximum data rate	$R_{L} = 3 k\Omega,$	$C_L = 250 \text{ pF}, \qquad V_{CC} = 3 \text{ V to } 4.5 \text{ V}$	1000			kbit/s
	(see Figure 1)	One DOUT switching	$C_L = 1000 \text{ pF}, V_{CC} = 3.5 \text{ V to } 5.5 \text{ V}$				KDII/S
t _{sk(p)}	Pulse skew ⁽³⁾	$C_{L} = 150 \text{ pF}$ to 2500 pF, R	L = 150 pF to 2500 pF, R_L = 3 kΩ to 7 kΩ, See Figure 2				ns
SR(tr)	Slew rate, transition region (see Figure 1)	$R_L = 3 \text{ k}\Omega$ to 7 k Ω , $C_L = 15$	$C_{L} = 150 \text{ pF to } 1000 \text{ pF}, \text{ V}_{CC} = 3.3 \text{ V}$			150	V/µs

Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V (see Figure 4). All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C. (1)

(2)

(3)Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.

ESD Protection

TERMINAL		TEST CONDITIONS		UNIT
NAME	NO.	TEST CONDITIONS	TYP	UNIT
		НВМ	±15	
DOUT	7, 14	IEC 61000-4-2 Air-Gap Discharge	±15	kV
		IEC 61000-4-2 Contact Discharge	±8	

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RECEIVER SECTION

Electrical Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
V_{OH}	High-level output voltage	$I_{OH} = -1 \text{ mA}$	$V_{CC} - 0.6$	$V_{CC} - 0.1$		V
V_{OL}	Low-level output voltage	I _{OL} = 1.6 mA			0.4	V
V	Positive-going input threshold voltage	$V_{CC} = 3.3 V$		1.5	2.4	V
V _{IT+}		$V_{CC} = 5 V$		1.8	2.4	v
v	Negative-going input threshold voltage	V _{CC} = 3.3 V	0.6	1.2		V
V _{IT}		$V_{CC} = 5 V$	0.8	1.5		v
V_{hys}	Input hysteresis (V _{IT+} – V _{IT–})			0.3		V
r _i	Input resistance	$V_1 = \pm 3 V$ to $\pm 25 V$	3	5	7	kΩ

(1) Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V (see Figure 4). (2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

Switching Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	TYP ⁽²⁾	UNIT
t _{PLH}	Propagation delay time, low- to high-level output	C = 150 pE	300	ns
t _{PHL}	Propagation delay time, high- to low-level output	C _L = 150 pF	300	ns
t _{sk(p)}	Pulse skew ⁽³⁾		300	ns

(1) Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V (see Figure 4). (2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

(3) Pulse skew is defined as |t_{PLH} - t_{PHL}| of each channel of the same device.

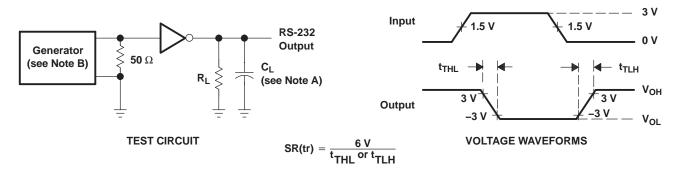
ESD Protection

TERMINAL		TEST CONDITIONS	ТҮР	
NAME	NO.	TEST CONDITIONS	ITP	UNIT
		НВМ	±15	
RIN	8, 13	IEC 61000-4-2 Air-Gap Discharge	±15	kV
		IEC 61000-4-2 Contact Discharge	±8	



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PARAMETER MEASUREMENT INFORMATION



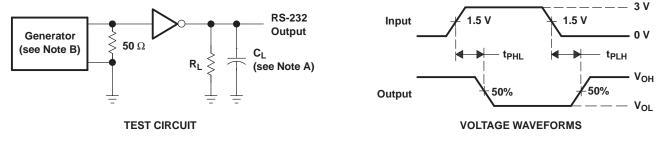
NOTES: A. C_L includes probe and jig capacitance.

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B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_0 = 50 \Omega$, 50% duty cycle, $t_r \le 10$ ns. $t_f \le 10$ ns.

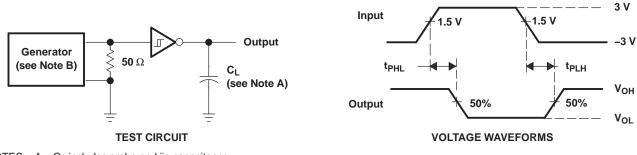
Figure 1. Driver Slew Rate



NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_0 = 50 \Omega$, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

Figure 2. Driver Pulse Skew



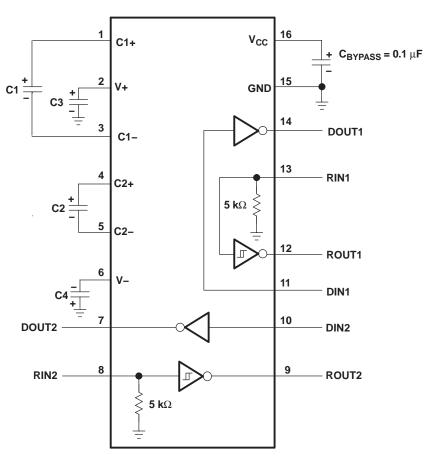
NOTES: A. C_L includes probe and jig capacitance. B. The pulse generator has the following characteristics: $Z_O = 50 \Omega$, 50% duty cycle, $t_r \le 10$ ns. $t_f \le 10$ ns.

Figure 3. Receiver Propagation Delay Times

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APPLICATION INFORMATION

V _{CC} vs	CAPACITOR VALUES	
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V _{CC}	C1	C2, C3, C4				
$\begin{array}{c} \textbf{3.3 V} \pm \textbf{0.3 V} \\ \textbf{5 V} \pm \textbf{0.5 V} \\ \textbf{3 V to 5.5 V} \end{array}$	0.1 μF 0.047 μF 0.1 μF	0.1 μF 0.33 μF 0.47 μF				

A. C3 can be connected to V_{CC} or GND.

Figure 4. Typical Operating Circuit and Capacitor Values



6-Feb-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN65C3232ED	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232E	Samples
SN65C3232EDB	ACTIVE	SSOP	DB	16	80	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU232E	Samples
SN65C3232EDBG4	ACTIVE	SSOP	DB	16	80	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU232E	Samples
SN65C3232EDBR	ACTIVE	SSOP	DB	16	2000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU232E	Samples
SN65C3232EDBRG4	ACTIVE	SSOP	DB	16	2000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU232E	Samples
SN65C3232EDE4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232E	Samples
SN65C3232EDR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232E	Samples
SN65C3232EDRG4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232E	Samples
SN65C3232EDW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232E	Samples
SN65C3232EDWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232E	Samples
SN65C3232EPW	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU232E	Samples
SN65C3232EPWE4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU232E	Samples
SN65C3232EPWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU232E	Samples
SN75C3232ED	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3232E	Samples
SN75C3232EDB	ACTIVE	SSOP	DB	16	80	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	0 to 70	MY232E	Samples
SN75C3232EDBR	ACTIVE	SSOP	DB	16	2000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	0 to 70	MY232E	Samples
SN75C3232EDR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3232E	Samples



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Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
SN75C3232EDW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3232E	Samples
SN75C3232EDWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3232E	Samples
SN75C3232EPW	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	0 to 70	MY232E	Samples
SN75C3232EPWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	0 to 70	MY232E	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

6-Feb-2020

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PACKAGE MATERIALS INFORMATION

www.ti.com

Texas Instruments

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C3232EDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN65C3232EDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
SN65C3232EPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN75C3232EDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN75C3232EDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
SN75C3232EPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TEXAS INSTRUMENTS

www.ti.com

PACKAGE MATERIALS INFORMATION

26-Feb-2019



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65C3232EDR	SOIC	D	16	2500	367.0	367.0	38.0
SN65C3232EDWR	SOIC	DW	16	2000	350.0	350.0	43.0
SN65C3232EPWR	TSSOP	PW	16	2000	367.0	367.0	35.0
SN75C3232EDR	SOIC	D	16	2500	367.0	367.0	38.0
SN75C3232EDWR	SOIC	DW	16	2000	350.0	350.0	43.0
SN75C3232EPWR	TSSOP	PW	16	2000	367.0	367.0	35.0

D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.



PW0016A



PACKAGE OUTLINE

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



PW0016A

EXAMPLE BOARD LAYOUT

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PW0016A

EXAMPLE STENCIL DESIGN

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

9. Board assembly site may have different recommendations for stencil design.



^{8.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

DW 16

GENERIC PACKAGE VIEW

SOIC - 2.65 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

7.5 x 10.3, 1.27 mm pitch

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





DW0016A



PACKAGE OUTLINE

SOIC - 2.65 mm max height

SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
- 5. Reference JEDEC registration MS-013.



DW0016A

EXAMPLE BOARD LAYOUT

SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DW0016A

EXAMPLE STENCIL DESIGN

SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



MECHANICAL DATA

MSSO002E - JANUARY 1995 - REVISED DECEMBER 2001

DB (R-PDSO-G**)

PLASTIC SMALL-OUTLINE

28 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
- D. Falls within JEDEC MO-150



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